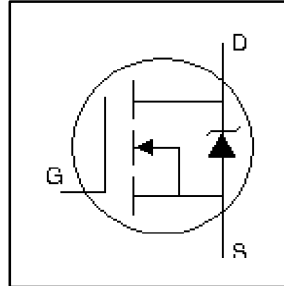


HEXFET® Power MOSFET

- Advanced Process Technology
- Ultra Low On-Resistance
- Surface Mount
- Available in Tape & Reel
- Dynamic dv/dt Rating
- Repetitive Avalanche Rated
- 175°C Operating Temperature



$$V_{DSS} = 100V$$

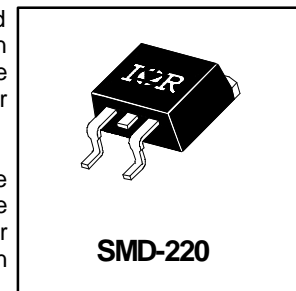
$$R_{DS(on)} = 0.04\Omega$$

$$I_D = 41A$$

Description

Fourth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The SMD-220 is a surface mount power package capable of accommodating die sizes up to HEX-4. It provides the highest power capability and the lowest possible on-resistance in any existing surface mount package. The SMD-220 is suitable for high current applications because of its low internal connection resistance and can dissipate up to 2.0W in a typical surface mount application.



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	41	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	29	
I_{DM}	Pulsed Drain Current ①	160	
$P_D @ T_C = 25^\circ C$	Power Dissipation	170	W
$P_D @ T_C = 25^\circ C$	Power Dissipation (PCB Mount)**	3.8	
	Linear Derating Factor	1.1	W/°C
	Linear Derating Factor (PCB Mount)**	0.025	
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulse Avalanche Energy ②	230	mJ
I_{AR}	Avalanche Current ①	41	A
E_{AR}	Repetitive Avalanche Energy ①	17	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.5	V/ns
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.90	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount)**	—	—	40	
$R_{\theta JA}$	Junction-to-Ambient	—	—	62	


** When mounted on 1" square PCB (FR-4 or G-10 Material).

For recommended footprint and soldering techniques refer to application note #AN-994.

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Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.10	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	—	—	0.04	Ω	$V_{GS} = 10V, I_D = 25A$ ①
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Transconductance	12	—	—	S	$V_{DS} = 50V, I_D = 25A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 100V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 80V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
Q_g	Total Gate Charge	—	—	110	nC	$I_D = 25A$
Q_{gs}	Gate-to-Source Charge	—	—	18		$V_{DS} = 80V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	—	42		$V_{GS} = 10V$, See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	13	—	ns	$V_{DD} = 50V$
t_r	Rise Time	—	77	—		$I_D = 25A$
$t_{d(off)}$	Turn-Off Delay Time	—	82	—		$R_G = 9.1\Omega$
t_f	Fall Time	—	64	—		$R_D = 2.0\Omega$, See Fig. 10 ④
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact
L_S	Internal Source Inductance	—	7.5	—		
C_{iss}	Input Capacitance	—	2500	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	630	—		$V_{DS} = 25V$
C_{riss}	Reverse Transfer Capacitance	—	130	—		$f = 1.0MHz$, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	41	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	160		
V_{SD}	Diode Forward Voltage	—	—	2.5	V	$T_J = 25^\circ\text{C}, I_S = 25A, V_{GS} = 0V$ ②
t_{rr}	Reverse Recovery Time	—	140	210	ns	$T_J = 25^\circ\text{C}, I_F = 25A$
Q_{rr}	Reverse Recovery Charge	—	0.79	1.2	μC	$di/dt = 100A/\mu s$ ③
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L_S+L_D)				

Notes:

① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)

③ $I_{SD} \leq 25A, di/dt \leq 170A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$

② $V_{DD} = 25V, \text{ starting } T_J = 25^\circ\text{C}, L = 3.1mH, R_G = 25\Omega, I_{AS} = 25A. (See Figure 12)$

④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.



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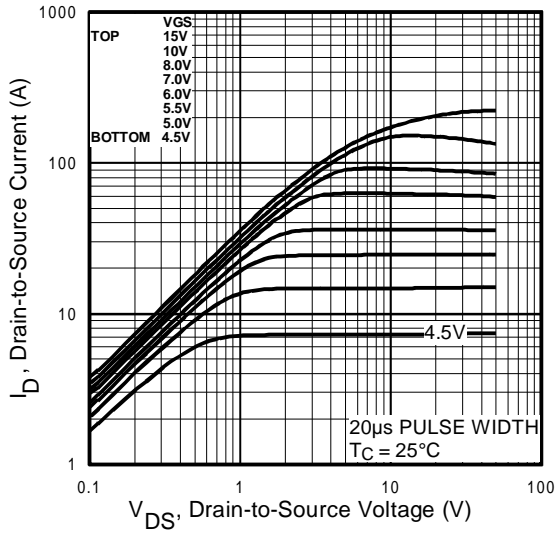


Fig 1. Typical Output Characteristics,
 $T_C = 25^\circ\text{C}$

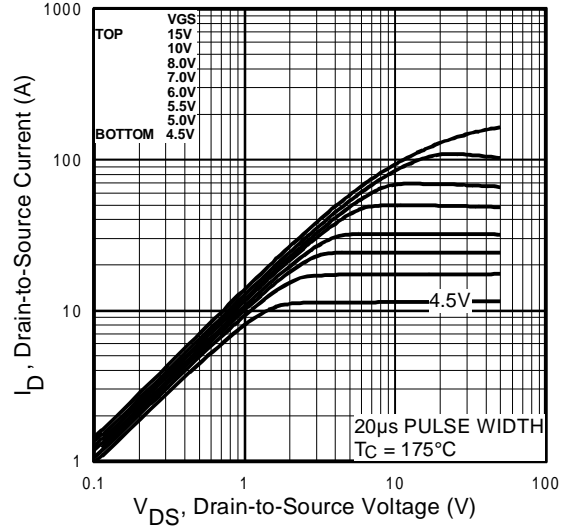


Fig 2. Typical Output Characteristics,
 $T_C = 175^\circ\text{C}$

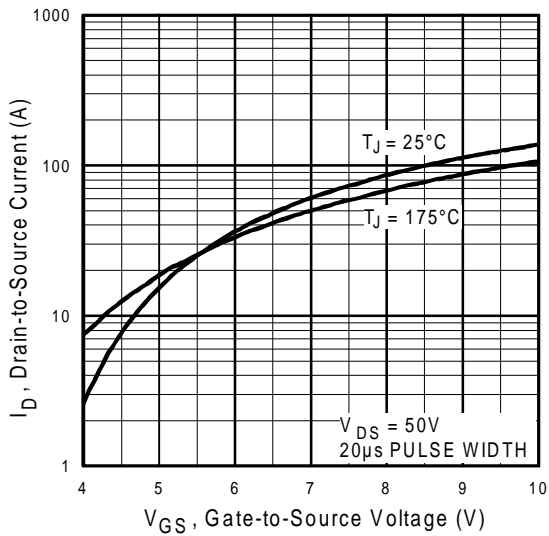


Fig 3. Typical Transfer Characteristics

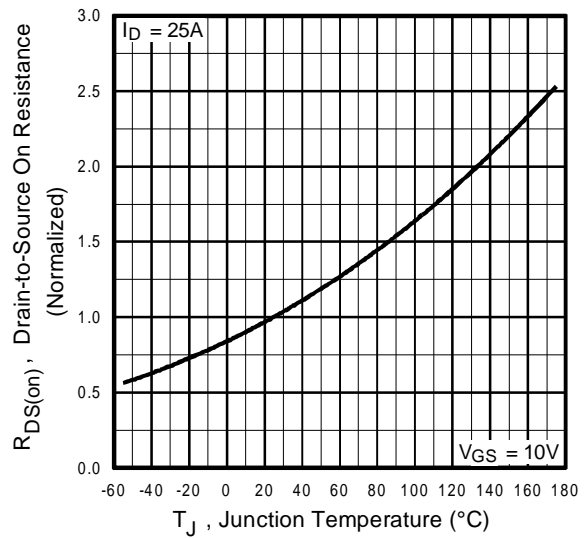


Fig 4. Normalized On-Resistance
Vs. Temperature

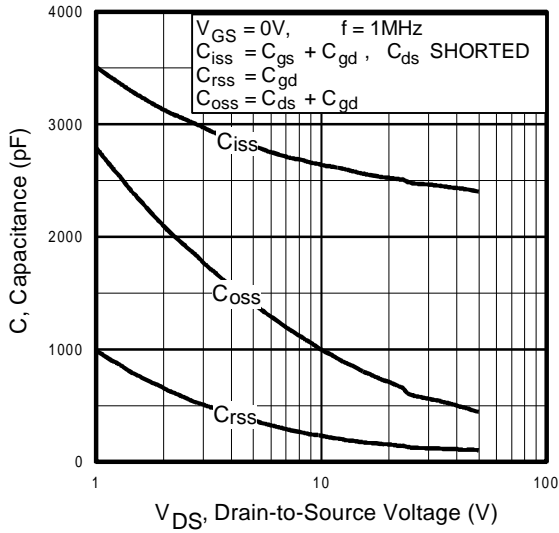


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

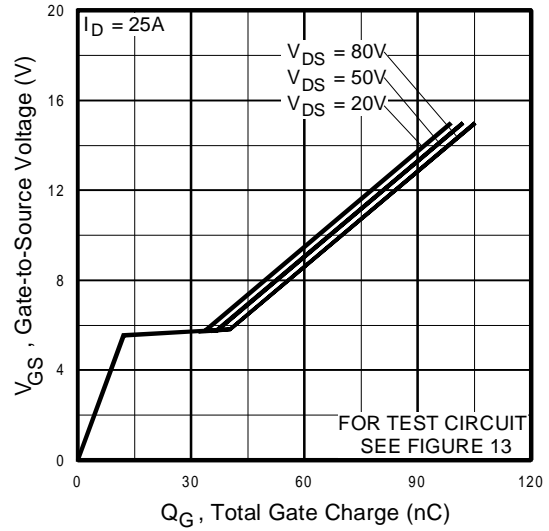


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

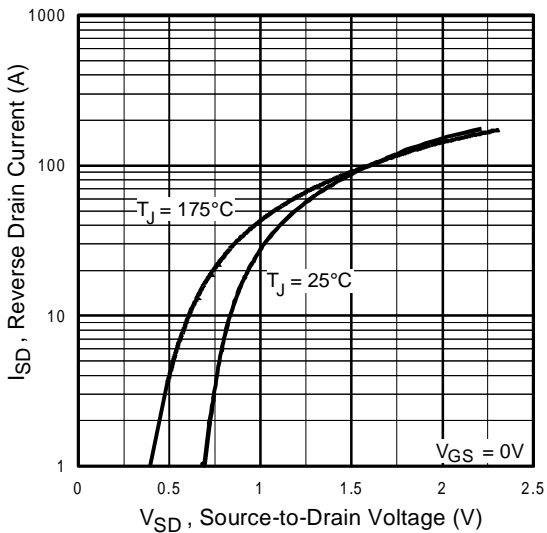


Fig 7. Typical Source-Drain Diode Forward Voltage

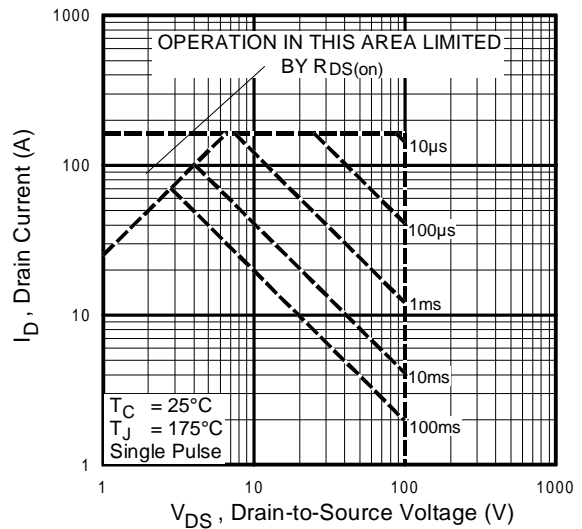


Fig 8. Maximum Safe Operating Area

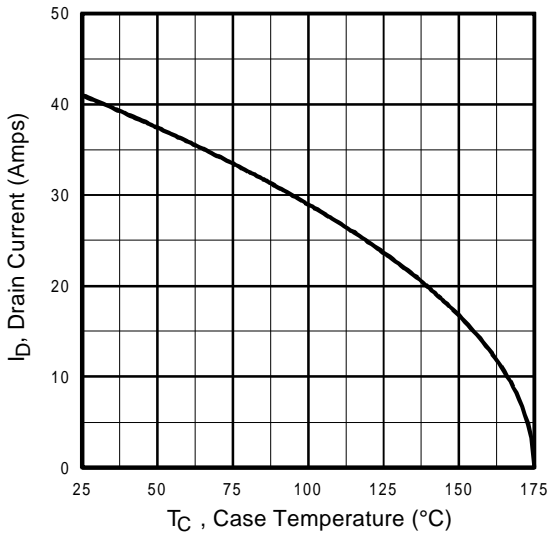


Fig 9. Maximum Drain Current Vs. Case Temperature

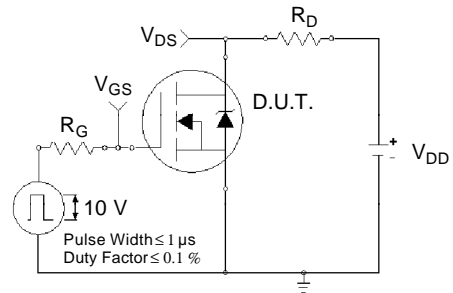


Fig 10a. Switching Time Test Circuit

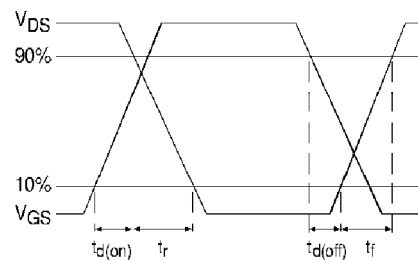


Fig 10b. Switching Time Waveforms

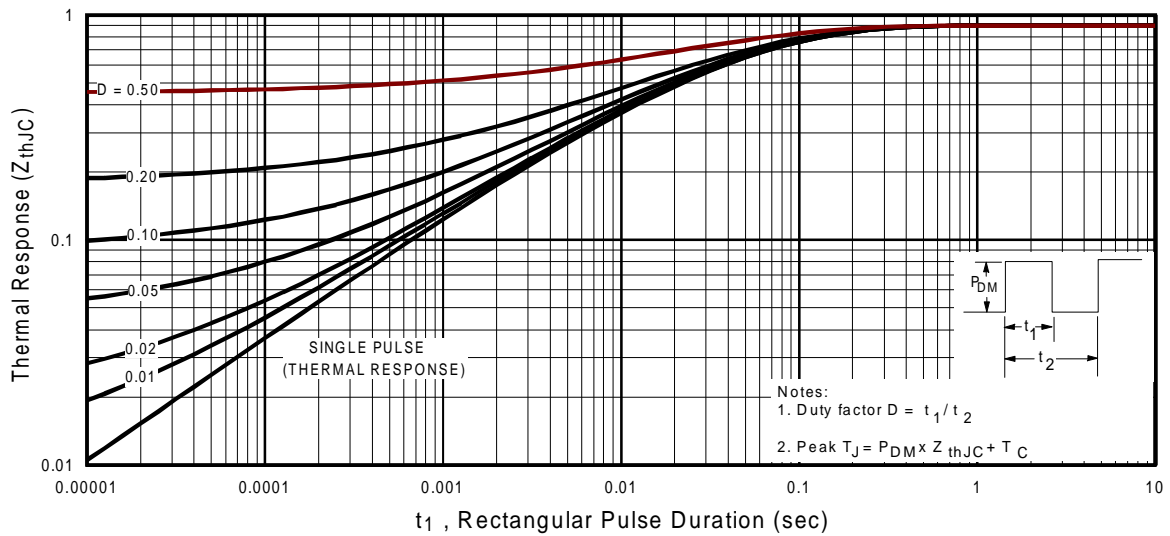


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

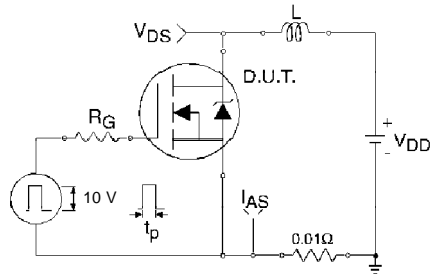


Fig 12a. Unclamped Inductive Test Circuit



Fig 12b. Unclamped Inductive Waveforms

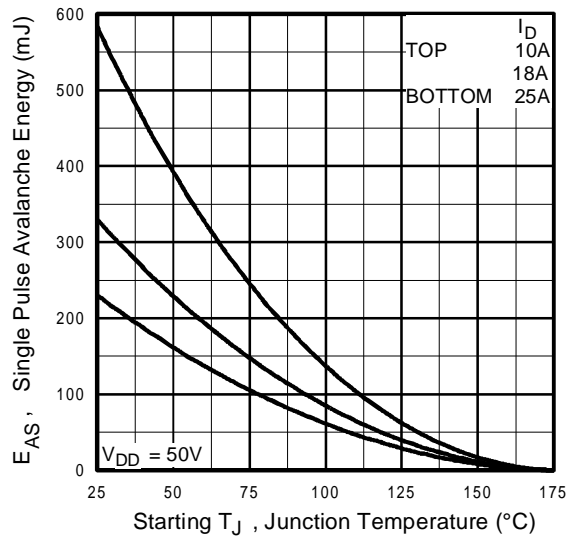


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

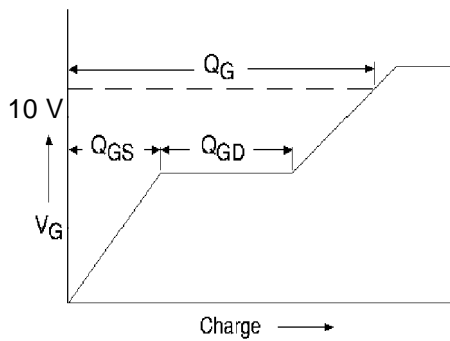


Fig 13a. Basic Gate Charge Waveform

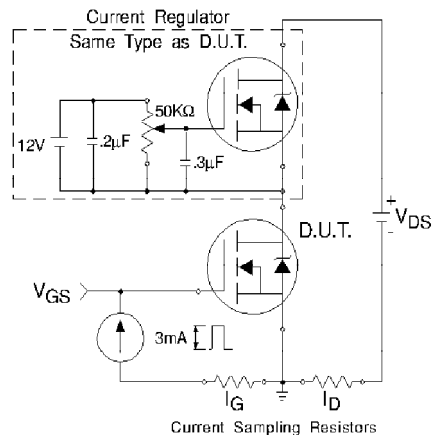


Fig 13b. Gate Charge Test Circuit

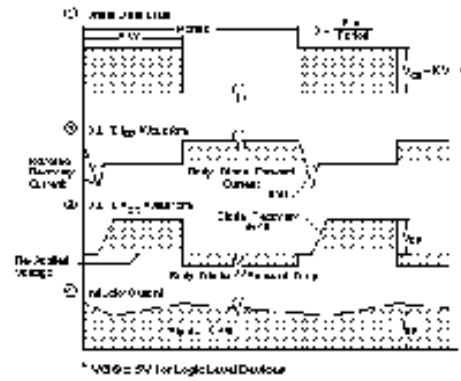
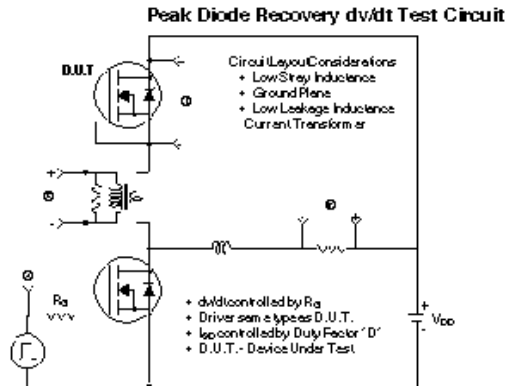
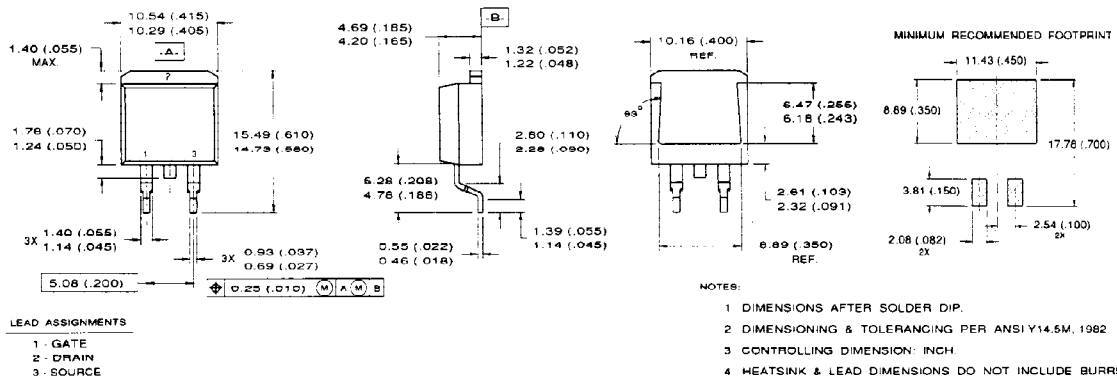


Fig 14. For N-Channel HEXFETS

Package Outline

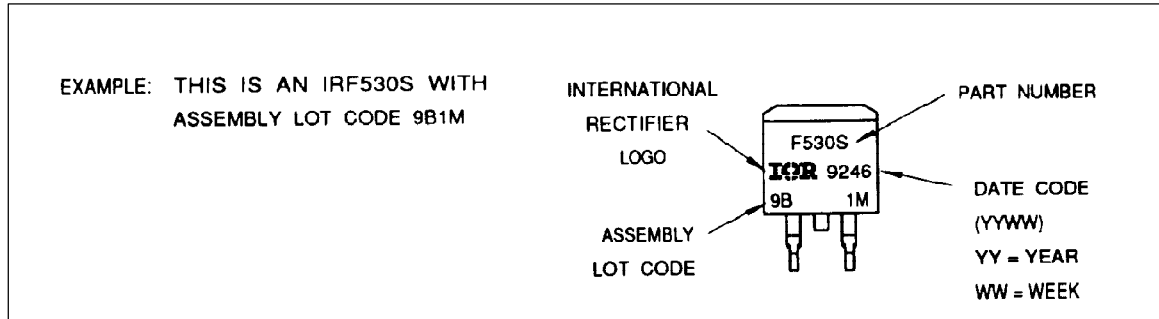
SMD-220 Outline



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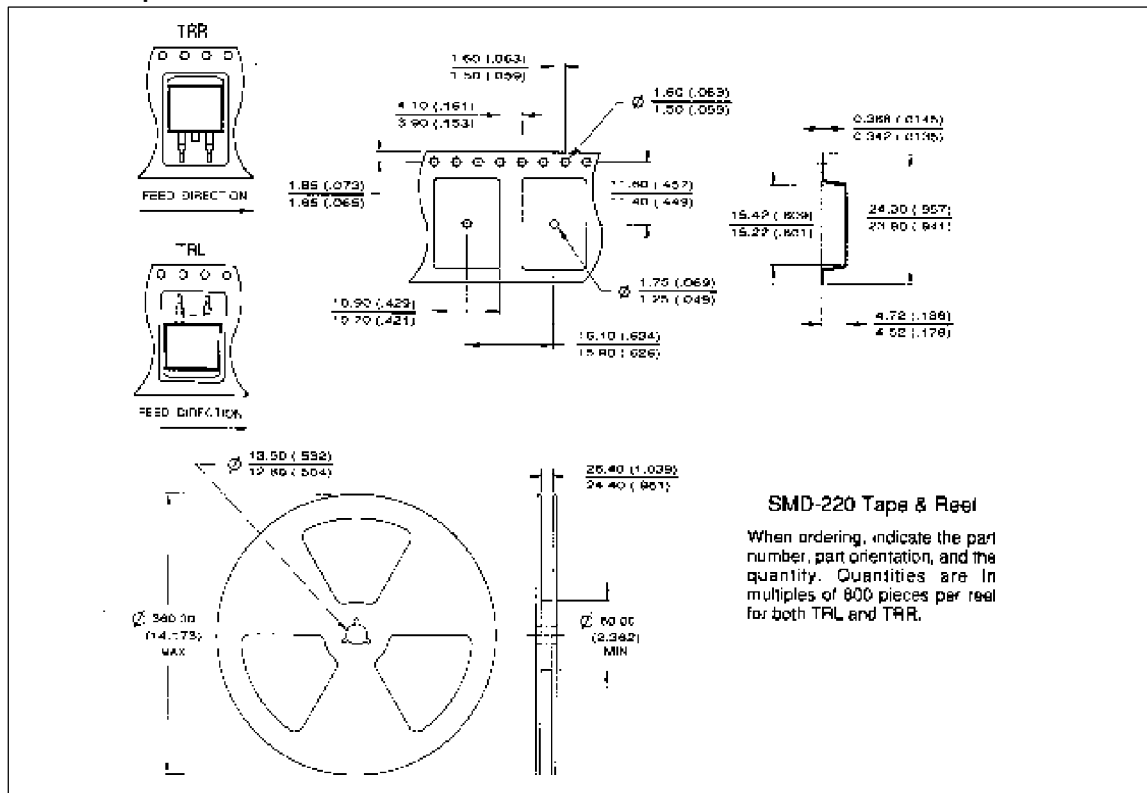


Part Marking Information



Package Outline

SMD-220 Tape and Reel



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EUROPEAN HEADQUARTERS: Hurst Green, Oxted, Surrey RH8 9BB, UK Tel: (44) 0883 713215
IR CANADA: 7321 Victoria Park Ave., Suite 201, Markham, Ontario L3R 3L1, Tel: (905) 475 1897 **IR GERMANY:** Saalburgstrasse 157, 61350 Bad Homburg Tel: 6172 37066 **IR ITALY:** Via Liguria 49, 10071 Borgaro, Torino Tel: (39) 1145 10111 **IR FAR EAST:** K&H Bldg., 2F, 3-30-4 Nishi-Ikeburo 3-Chome, Toshima-Ki, Tokyo 171 Tel: (03)3983 0641 **IR SOUTHEAST ASIA:** 315 Outram Road, #10-02 Tan Boon Liat Building, 0316 Tel: 65 221 8371

Data and specifications subject to change without notice.